

# Multiple scattering of 855 MeV electrons in amorphous and crystalline silicon: simulations versus experiment

Germán Rojas-Lorenzo, Jesús Rubayo-Soneira, and Maykel Márquez-Mijares  
*Instituto Superior de Tecnologías y Ciencias Aplicadas, Universidad de La Habana (InSTEC-UH),  
Ave. Salvador Allende 1110, Plaza de la Revolución, Habana 10400, Cuba.*

Andrei V. Korol and Andrey V. Solov'yov  
*MBN Research Center, Altenhöferallee 3, 60438 Frankfurt am Main, Germany.*

The angular distribution function of multiple scattering experienced by 855 MeV electrons passing through an amorphous silicon plate and an oriented silicon crystal has been studied by means of relativistic molecular dynamics simulations using two types of the potentials that describe electron-atom interaction. The differences in the angular distributions of the beam particles in both media are analysed. The results obtained are compared to the experimental data and to the results of Monte Carlo simulations.

## I. INTRODUCTION

In the 1960s, Lindhard published a comprehensive theoretical study on the influence of crystal structure on the motion of energetic charged particles [1]. He revealed and described directional effects for the projectiles incident on oriented crystals which lead to the governed motion due to inhomogeneity, anisotropy and lack of randomness in the medium. By introducing the concept of the continuous potential of an atomic string or plane in a crystal Lindhard explained the channeling phenomenon (i.e. the guided motion of charged projectiles in the vicinity of major crystallographic axis or planes) that had been detected earlier in the experiments on propagation lengths for heavy ions in aluminum [2]. Since then studies of the channeling phenomenon, or more generally, of passage of ultra-relativistic particles through oriented crystals of different geometry (linear, bent, periodically bent crystals) have expanded to form a broad field of theoretical and experimental research (see, e.g., [3]) as well as of a number of applications. The latter include, for example, beam manipulation, – steering, focusing, collimation, splitting, and extraction, by means of crystals (see, e.g., Refs. [4–8] and references therein). Another promising potential application concerns realisation of novel intensive gamma-ray light sources operating at photon energies within MeV-GeV range that can be constructed by exposing oriented crystals to beams of ultra-relativistic charged projectiles [9–11].

Regularity in positions of crystal constituents modifies multiple scattering and radiative processes for a charged projectile particle as compared to its passage through an amorphous medium [12]. This occurs for the channeling particles as well as for those experiencing the over-barrier motion, i.e. moving across crystal planes / axes.

Recently, an experimental observation was reported [13] of the reduction of multiple scattering for high-energy positively charged particles experiencing planar channeling in single crystals. The measurements have shown that the root-mean-square planar angle of multiple scattering in the plane normal to the plane of the

channeling is less than that for the over-barrier particles in the same crystal. The explanation presented refers to the specific feature of the channeling phenomenon of positively charged projectiles. Their interaction with the crystal atoms is repulsive, therefore, in the planar regime they channel in between two adjacent planes. If the amplitude of the channeling oscillations is smaller than  $d/2 - a_{\text{TF}}$  ( $d$  is the interplanar distance and  $a_{\text{TF}}$  is the Thomas-Fermi radius of the atom) then channeling occurs in the spatial region with the electron volume density less (on average) than in the amorphous medium. As a result, such particles can penetrate large distance into a crystal and exit from the crystal at relatively small scattering angle.

In another recent experiment [14] carried out at the Mainz Mikrotron (MAMI) facility the observation has been made of the reduction of multiple scattering angle of 855 MeV electrons incident at a small angle with respect to the  $\langle 001 \rangle$  axis in a crystalline silicon as compared to that in an amorphous target. It is indicated in the cited paper that a projectile particle while moving in a crystalline environment can interact either with individual atoms as in an amorphous medium (incoherent scattering) or with atoms arranged in strings or in planes (coherent scattering). Section 2 in the paper provides quantitative analysis of the conditions to be met for the incident angle of particle's momentum  $\vec{p}_0$  with respect to the axis (plane) that facilitate the coherent scattering and, as a result, lead to the decrease in the scattering angle. The effect of coherent scattering suppression (CSS) that occur at certain crystal orientations has been observed experimentally as well as modelled via Monte Carlo simulations [14].

In this paper we present an independent analysis of the multiple scattering process of electrons in the crystalline and amorphous silicon targets. The analysis is based on the results of the relativistic classical molecular dynamics simulations performed by means of the MBN EXPLORER package [15–18]. The parameters of the targets as well as the characteristic of the electron beam (energy, angular divergence and orientation with respect to the crystal)

used in the simulations correspond to those used in the experiment [14] (see Section II for details). In Section III the numerical results obtained are compared with the experimental data collected at MAMI. In Section IV, some conclusions of this work are summarized and future perspectives are presented.

## II. METHODOLOGY

A number of numerical tools have been developed within frameworks of different theoretical approaches to simulate various phenomena occurring during passage of ultra-relativistic projectiles through oriented crystals and amorphous solids (see Ref. [19] for an overview of the most recent ones). In many cases, a rigorous description can be achieved within the classical formalism by considering particles' trajectories. For numerical modeling of channeling and related phenomena beyond the continuous potential framework we utilize the multi-purpose computer package MBN EXPLORER [15, 16, 18, 20] and a supplementary special multitask software toolkit MBN-STUDIO [17]. Developed originally as a universal program for investigating structure and dynamics of molecular systems at various spatial scales, ranging from atomistic up to macroscopic, the package allows for a computation of relativistic projectile motion in various environments including crystalline structures [20]. The simulation procedure accounts for the interaction of a projectile particle with all atoms in the environment. A number of various interatomic potentials implemented in the package enables rigorous simulations of different media. The algorithms implemented allow for modelling passage of the particles over macroscopic distance with atomistic accuracy. The package serves as a powerful numerical tool to explore relativistic dynamics in crystals and amorphous systems. Its efficiency and reliability have been evaluated for channeling of ultra-relativistic projectiles within the energy range of sub-GeV to tens of GeV in straight, bent, periodically bent crystals, and amorphous medium (see the review paper [19] and references therein).

The simulation procedure of the motion of an ultra-relativistic particle of energy  $\varepsilon$ , charge  $q$  and mass  $m$  is carried out within the framework of classical relativistic mechanics. MBN EXPLORER integrates relativistic equations of motion that are written as follows:

$$\dot{\vec{r}} = \vec{v}, \quad \dot{\vec{v}} = \frac{1}{m\gamma} \left( \vec{F} - \frac{\vec{v}(\vec{v} \cdot \vec{F})}{c^2} \right). \quad (1)$$

Here  $\vec{r} = \vec{r}(t)$  and  $\vec{v} = \vec{v}(t)$  stand for the particle's position vector and velocity at instant  $t$ ,  $\gamma = \varepsilon/mc^2$  is the relativistic Lorentz factor. The force  $\vec{F} = -q\partial U(\vec{r})/\partial\vec{r}$  acting on the projectile is due to the electrostatic field created by atoms of the medium.

At each integration step the electrostatic potential  $U(\vec{r})$  is computed as the sum of potentials  $U_{\text{at}}$  of indi-

vidual atoms

$$U(\vec{r}) = \sum_j U_{\text{at}}(|\vec{r} - \vec{R}_j|). \quad (2)$$

Here  $\vec{R}_j$  denotes a position vector of the  $j$ th atom. The code allows for the evaluation of atomic potentials using approximations proposed by Molière [21] and Pacios [22]. The Pacios approximation provides basically the same results as frequently used Doyle-Turner scheme [23] but in contrast to the latter it leads to the correct behaviour  $\propto 1/r$  of  $U_{\text{at}}$  at small distances (see, e.g., Ref. [24]). More details on the algorithms implemented in MBN EXPLORER are given [15, 19].

In the current paper we consider propagation of 855 MeV electrons through crystalline and amorphous Silicon targets the parameters of which were chosen in accordance with the experiment carried out at the MAMI facility [14]. In the case of the oriented crystalline target the simulations have been performed for the electron beam incident on the crystal along the directions probed experimentally as well as along the directions that were not explored in the experimental setup. This allows us to compare the simulated dependencies with the experimentally measured data on the angular distribution of deflected electrons as well as to investigate the evolution of the distribution with variation of the relative orientation of the crystal and the beam. The atomistic approach implemented in MBN EXPLORER enables simulation of the trajectories of charged particles entering a crystal along any chosen direction. Taking advantage of this capability, we have specifically studied the beam incident on a crystal at some angles with respect to the (001) crystallographic axis.

In Ref. [14] the directions of the incident 855 MeV beam that lead to CSS have been specified in terms of the planar angles  $\Theta_v$ ,  $\Theta_h$  that can be used instead of the polar angles  $\Theta = (\Theta_v^2 + \Theta_h^2)^{1/2}$ ,  $\phi = \tan^{-1}(\Theta_v/\Theta_h)$  measured with respect to the (001) direction. These angles are defined as follows: (i)  $\Theta_v$  is the angle between  $\vec{p}_0$  and the (110) plane, and (ii)  $\Theta_h$  is the angle between  $\vec{p}_0$  and the (1 $\bar{1}$ 0) plane. It was estimated that the angles' values are to be chosen from the intervals (in mrad):

$$18 < \Theta_h < 43, \quad 2 < \Theta_v < 4.3. \quad (3)$$

The experiment was carried out using for a 34.2  $\mu\text{m}$  thick silicon crystal. The CSS effect in the angular distribution of the deflected electrons was observed for  $\Theta_h = 34.9$  mrad and  $\Theta_v = 3$  mrad. The data obtained was compared to the angular distribution measured in 32.76  $\mu\text{m}$  thick amorphous silicon.

In our simulations other values of  $\Theta_h$  and  $\Theta_v$ , that are close to this direction, have been considered. To reproduce the experimental results [14] we have studied the effect of multiple scattering suppression that takes place at certain orientations of the crystalline target. The goal was to determine the necessary conditions for CSS to occur, which typically happens at the incident angle much

greater than Lindhard's critical angle,  $\Theta_L$ . Written in terms of the depth  $U_0$  of the continuous interplanar potential  $\Theta_L$  reads  $\Theta_L = (2U_0/\varepsilon)^{1/2}$ . For a 855 MeV projectile in a (110) channel in a silicon crystal ( $U_0 \approx 20$  eV) this estimate provides  $\Theta_L \approx 0.22$  mrad.

In the Section below we present and discuss the results of simulations. Basing on the information provided on the experimental setup, the simulations have been carried out for several values of the angles  $\Theta_h$  and  $\Theta_v$  within the intervals specified by Eq. (3). Four sets of the simulations have been performed for the crystalline target. Two sets refer to the fixed value of  $\Theta_v$  (2 and 3 mrad, correspondingly) and  $\Theta_h$  varied within the specified interval. In another pair of sets the value of  $\Theta_v$  was scanned over the interval while  $\Theta_h$  was fixed at 33 and 34.9 mrad.

For each pair ( $\Theta_v, \Theta_h$ ) considered a large number,  $N \approx 4 \times 10^4$ , of trajectories were simulated. In the course of the simulations the transverse velocity of the particles at the solid target entrance were generated taking into account the Gaussian distributions of the beam particle due to the beam divergencies. The following values of the standard deviations of the divergences of the 855 MeV electron beam at MAMI were used:  $\sigma'_h = 70$  and  $\sigma'_v = 30$   $\mu$ rad. General methodology implemented in MBN EXPLORER to generate particles' trajectories in an atomic environment accounts for randomness in sampling the incoming projectiles (the key factors here are beam size, divergence and direction with respect to the crystal orientation) as well as in displacement of the lattice atoms from the nodal positions due to the thermal vibrations (see Refs. [19, 20] for details). As a result, each trajectory corresponds to a unique atomic environment and, therefore, all simulated trajectories are statistically independent and can be analyzed further to quantify the process of interest, the multiple scattering process in particular.

For the sake of comparison, the same number of trajectories have been simulated for 855 MeV electrons passing through amorphous silicon.

To simulate the amorphous environment the following procedure was used. In MBN EXPLORER, when constructing a crystalline structure the position vectors of atomic nuclei are generated with account for random displacement from the nodes due to thermal vibrations corresponding to given temperature  $T$ . By introducing unrealistically large value of the root-mean-square thermal vibration amplitude  $u_T$  (for example, comparable to the lattice constant  $a$ ) it is possible to consider large random displacements, i.e. the structure will resemble an amorphous medium. Additionally, one can change the value of the unit cell volume to make the volume density of atoms equal to the volume density in the amorphous medium. To simulate amorphous silicon medium  $u_T$  was set to 2  $\text{\AA}$ . Taking into account that a unit cell of a silicon crystal (with  $a = 5.43$   $\text{\AA}$ ) contains 8 atoms, the quoted value of  $u_T$  is sufficient enough to ensure randomness of atomic positions in the sample.

### III. RESULTS AND DISCUSSIONS

The simulated trajectories have been statistically analyzed to provide quantitative data on the particles' distribution in the following two planar angles:<sup>1</sup>

- (i)  $\vartheta_v$  – the angle between projectile's momentum  $\vec{p}$  at the target's exit and the (110) plane;
- (ii)  $\vartheta_h$  – the angle between  $\vec{p}$  and the (1 $\bar{1}$ 0) plane.

These planar angles are measured in two perpendicular planes, therefore, the total (round) scattering angle  $\theta$  with respect to the  $\langle 001 \rangle$  axis is calculated as  $\theta = (\vartheta_v^2 + \vartheta_h^2)^{1/2}$ .

The distribution of deflected particles in either of the planar angles can be derived from the distribution in  $\theta$ . The latter, following Ref. [14], we consider within the framework of the Molière scattering model [21] (see also a paper by Bethe [25]). The details of the derivation are presented in Appendix A. For a planar angle (in the formula below  $\vartheta$  stands for either of  $\vartheta_v, \vartheta_h$ ) the probability distribution function (PDF) that represents the angular distribution function of the particles experienced multiple scattering, can be written as follows:

$$\text{PDF}(\vartheta) = \frac{1}{N} \frac{dN(\vartheta)}{d\vartheta} = \mathcal{A} \sum_{n=0}^{\infty} \left( \frac{\chi_c^2}{2\theta_s^2} \right)^n \frac{1}{n!} \times \int_0^{\infty} du e^{-u^2/4} \cos \left( u \frac{\vartheta}{\sqrt{2\theta_s^2}} \right) \left( \frac{u^2}{4} \ln \frac{u^2}{4} \right)^n \quad (4)$$

where  $dN(\vartheta)$  denotes a number of particles that are scattered by a planar angle lying within the interval  $[\vartheta, \vartheta + d\vartheta]$ ,  $N$  is the total number of particles,  $\mathcal{A} = 1/\pi (2\theta_s^2)^{1/2}$  is the normalization factor, and parameter  $\chi_c$ , dependent on particle's energy and target's thickness, volume density and atomic charge number, is defined in Appendix A, Eq. (A.2). The parameter  $\theta_s$  is to be determined by fitting the PDF function to the simulated data. To fit the data generated in the simulations with the Molière PDF the Levenberg-Marquardt algorithm [26, 27] was implemented. The term with  $n = 0$  corresponds to the normal (Gaussian) distributions in which  $\theta_s$  plays the role of standard deviation. The terms  $n \geq 1$ , which provide the correction to the normal distribution, can be effectively evaluated numerically (see Appendix A for more details). In the fitting procedure the series in (4) were cut off at  $n = 12$ .

The CSS effect, which was reported in the experiment, has also been observed in our simulations within a specific region characterized by  $\Theta_h = 34.9$  mrad and  $\Theta_v = 3$  mrad. Figure 1 compares the PDFs as functions of the vertical scattering angle  $\vartheta_v$  plotted as histograms using the data obtained from the simulations for the crystalline (black curve with open circles) and amorphous (red curve

<sup>1</sup> In Ref. [14] the notations  $\vartheta_x, \vartheta_y$  are used for the angles  $\vartheta_v, \vartheta_h$

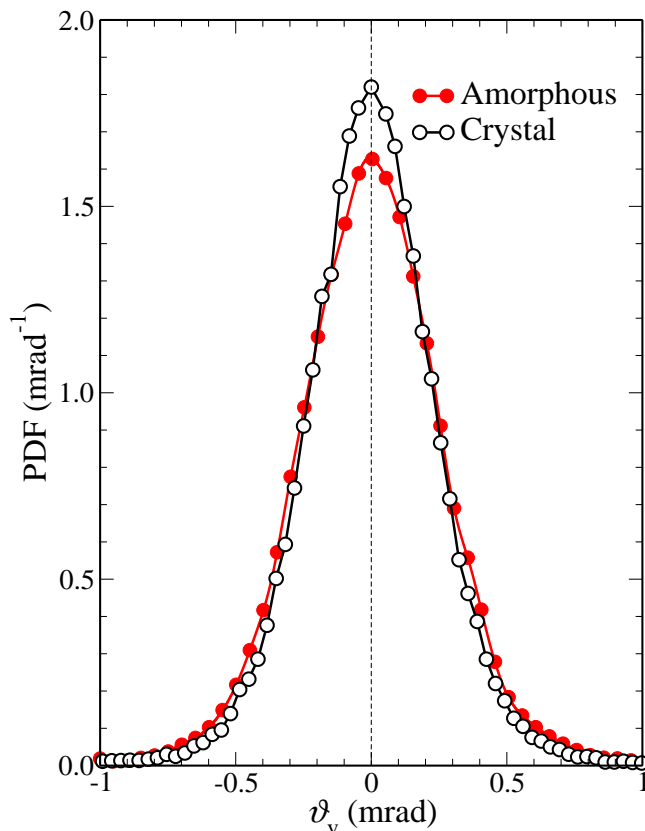


FIG. 1. The probability density function (PDF) versus vertical scattering angle  $\vartheta_v$  plotted for amorphous (red line, filled circles) and crystalline silicon (black line, open circles). The data refer to the incident angles  $\Theta_h = 34.9$  mrad and  $\Theta_v = 3$  mrad.

with filled circles) silicon targets. It can be observed that the PDF values are higher for the crystal silicon compared to the amorphous one in the domain off small scattering angles  $|\vartheta_v| \lesssim 0.3$  mrad. Notably, the peak value of the PDF obtained in the simulations is  $1.82 \text{ mrad}^{-1}$  for the crystal which is slightly higher  $1.67 \text{ mrad}^{-1}$  for the amorphous target. This suggests that the crystalline silicon exhibits a lower scattering intensity within the specified range of scattering angles compared to the amorphous state. However, it is important to note that our simulation results show a slight broadening of the calculated PDF compared to the experimentally observed data.

Following Ref. [14], one can consider the difference of PDFs for the crystal and amorphous Si,  $\text{PDF}_{\text{cr}} - \text{PDF}_{\text{am}}$ , to quantify further the changes in the angular distributions of electrons passing through the two types of medium. This difference allows one to numerically evaluate the dissimilarity in the PDFs for the two types of medium providing a quantitative measure of the disparity in scattering behaviour as well as to gain valuable insights into the structural effects that influence the electron multiple scattering.

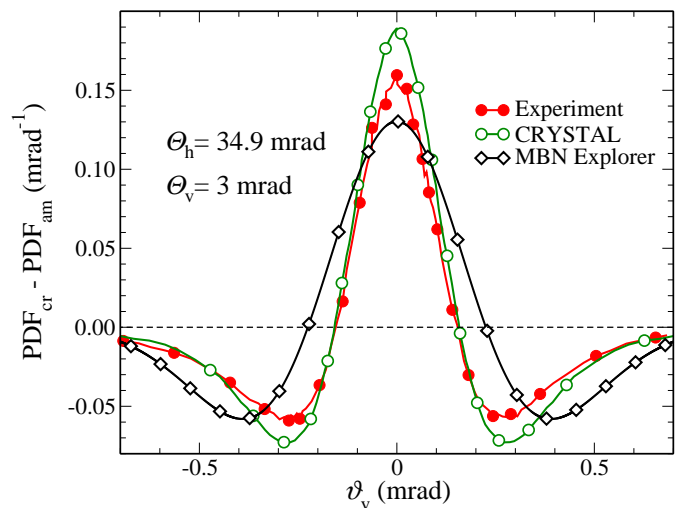


FIG. 2. The difference of PDFs for the beam deflected by the silicon crystal and the amorphous target. Solid red line with filled circles and solid green line with open circles stand for the Experimental data (red line with filled circles) and the results of the CRYSTAL code (green line with open circles) are from Ref. [14]. Black line with open diamonds show the data simulated with MBN EXPLORER. In all cases the incident angles are  $\Theta_v = 3$  mrad and  $\Theta_h = 34.9$  mrad.

Figure 2 shows the variations in the PDF for the beam deflected by the crystal and amorphous targets. The variations obtained by means of MBN EXPLORER (black curve with diamonds) are compared to the experimental data (red line with filled circles) and to the results of the simulations with the CRYSTAL code [28] (green line with open circles) both taken from Ref. [14]. All data presented correspond to the incident angles  $\Theta_v = 3$  mrad and  $\Theta_h = 34.9$  mrad in the case of the crystalline target. The results of the simulations performed with MBN EXPLORER shown in the figure correspond to the Molière potential. Similar simulations have been performed with the Pacios potential (not shown in the figure) and it was that the differences between the two sets of data is less than 0.4%. We consider this as a demonstration of the robustness of our results. All three curves presented in the figure show similar behaviour. However, there are some differences between the currents simulation and the experimental results regarding, in particular, the width of the central peak of the function.

In our simulations we aimed to investigate the CSS effect over a wide range of the incident angles. Therefore, we have explored values beyond the optimal ranges indicated in Eq. (3) to thoroughly understand the scattering behaviour and to assess the robustness of the observed CSS effect.

Following the approach adopted in the experiment [14], we have conducted scans over the incident angles aiming at exploring the variation in the scattering behaviour of electrons in crystalline silicon in comparison with the amorphous medium. To this end, two sets of simulations



have been carried out. In the first set, the the vertical incident angle was fixed at  $\Theta_v = 3$  mrad whereas the horizontal angle was varied within the interval  $8.7 \leq \Theta_h \leq 52$  mrad. Similarly, in the second set the angle  $\Theta_h = 34.9$  mrad was fixed and the angular distributions was explored in the range  $1 \leq \Theta_v \leq 10$  mrad. These scanning parameters allowed us to investigate the angular dependence of the scattering phenomenon and to identify notable trends or/and extrema of the PDFs. For all combinations  $(\Theta_h, \Theta_v)$  considered the simulations were performed using both the Molière and Pacios potentials. The PDF obtained were practically independent on the potential used. The minimum value of  $\theta_s$  due to the coherent scattering has been found at  $\Theta_h = 34.9$  mrad and  $\Theta_v = 2$  mrad. This observation provided a crucial starting point for further analysis and understanding of the scattering behavior in silicon. To quantify the scattering distribution and to derive the PDF for scattered electrons additional scans were performed fixing  $\Theta_v = 2$  mrad and varying  $\Theta_h$  as well as scanning over  $\Theta_v$  while fixing  $\Theta_h = 33$  mrad. These scans allowed us to capture the variations in the PDF as we explored different scattering angles.

Figure 3 shows the variation of  $\theta_s$  as a function of one of the incident angles ( $\Theta_h$  in left graph and  $\Theta_v$  in right graph) while fixing the second incident angle (see the values indicated at the top of each graph). Solid and dashed lines stand for the crystalline and the amorphous targets, respectively. The results of our simulations are shown as open diamond symbols connected with black lines. Statistical uncertainties due to the finite number of simulated trajectories are indicated with error bars. The data reported in Ref. [14] are shown with filled circles connected with red lines (the experimental data) and with open circles connected with green lines (the results of simulation with the CRYSTAL code [28]). For the sake of comparison we also present the value of multiple scattering angle calculated for the amorphous silicon by means of Eqs. (34.16), (34.25) and (34.26) from the review by Particle Data Group [30] (see also Appendix B). This value, shown in both graphs with dashed-dotted line, corresponds to the mass thickness  $T \propto NL$  ( $N$  is the volume density,  $L$  is the thickness) that one can calculate from the information on the samples used in the experiment indicated Ref. [14]. It is indicated that mass thicknesses of the crystalline and amorphous samples were equal, therefore,  $T \propto N_{cr}L_{cr}$  with  $L_{cr} = 32.76 \mu\text{m}$  as quoted and  $N_{cr} = 8/(5.43 \text{ \AA})^3 = 5.00 \times 10^{22} \text{ cm}^{-3}$ .

One can state that there is a close similarity between our results and the experimentally measured data when comparing the profiles of the dependencies  $\theta_s(\Theta_h)$  and  $\theta_s(\Theta_v)$  for the crystal target. Indeed, the simulations have successfully captured all the essential trends in the dependencies and reproducing the key features observed in the experiment.

To be noted, nevertheless, is a systematic difference in absolute values of the simulated and measured data on  $\theta_s$ . For both crystalline and amorphous targets the simu-

lations produce higher values with the excess of ca 0.03-0.035 mrad on average.<sup>2</sup> The reason for this discrepancy is unclear. One can speculate that it might be related to some specific algorithm in the statistical processing of the results. For example, it was noted in Ref. [14] that to compare directly the results obtained by means of the CRYSTAL code to the experimental data the former are to be convoluted with the angular distribution of the beam. However, this is definitely not the issue in connection with our methodology since the beam divergence has been explicitly accounted for to randomize "entrance conditions" for the incident particles (in both vertical and horizontal directions). The feature that might be relevant but deserves further analysis concerns the algorithm implemented in MBN EXPLORER to simulate crystalline and amorphous environment. As mentioned in the last paragraph in Section II (see [19, 20] for more details) the atomic displacements from the nodal positions are randomly generated. For doing this the normal distribution with the variance equal to  $u_T$  is used. This algorithm does not exclude non-physical events when two (or more) atoms will be located in close vicinity to each other. This will result in the (local) increase in the scattering angle which inevitably will affect the multiple scattering angle as well.

#### IV. CONCLUSION

By means of relativistic all-atom molecular dynamics implemented in the MBN EXPLORER software package the passage of ultra-relativistic electrons through crystalline and amorphous silicon media has been simulated. The parameters of the 855 MeV electron beam and the thickness of the silicon targets utilized in the simulations correspond to those used in the experiment [14] which revealed broad angular anisotropy of multiple scattering in the crystal. For each incident geometry considered a sufficiently large number ( $\approx 4 \times 10^4$ ) of statistically independent trajectories has been generated. The statistical analysis carried out resulted in calculation of the probability distribution functions (PDF) that allowed us to quantify the process of multiple scattering in terms of the planar scattering angles. To double check the results, the simulations and the analysis have been performed employing both the Molière and Pacios potentials for the electron-Si-atom interaction. The dependencies of the scattering angle  $\theta_s$  on both the horizontal  $\Theta_h$  and vertical  $\Theta_v$  incident angles turned out to be virtually insensitive to the choice of the potential.

We have observed the differences in angular distributions of electrons deflected by the crystalline and the

<sup>2</sup> Also to be noted is that for the amorphous target our result and the experimental data both differ from the commonly used estimate [30] of the multiple scattering angle, see the dashed-dotted lines in both graphs in Fig. 3.

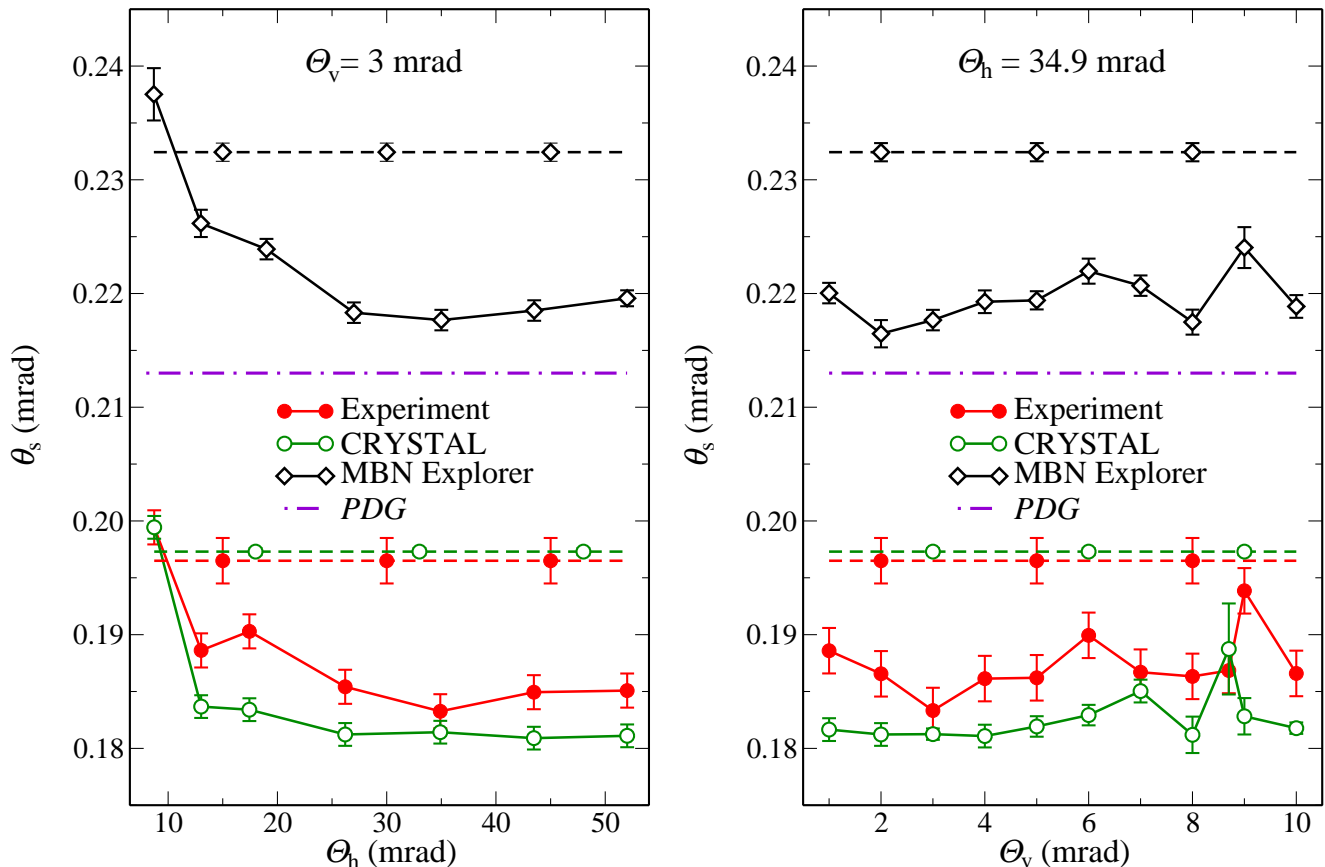


FIG. 3. *Left*: Multiple scattering angle  $\theta_s$  as a function of the horizontal (left) and vertical (right) incident angles. Solid lines stand for the crystalline target, dashed lines indicate the results for the amorphous medium. Experimental data (red lines, filled circles) and results of simulations with the CRYSTAL code (green lines, open circles) are from Ref. [14]. The results of current simulations (black lines with diamonds) correspond to the Molière potential. For the crystal Si, the incident angles are fixed at:  $\Theta_v = 3$  mrad (left) and  $\Theta_h = 34.9$  mrad (right). In both graphs dashed line with dots denotes the rms scattering angle calculated using the formula presented in the review by Particle Data Group (PDG) [30].

amorphous targets that were predicted, explained and measured in Ref. [14]. Our results exhibit a high degree of agreement with the experimental data in terms of the profiles of the dependencies  $\theta_s(\Theta_h)$  and  $\theta_s(\Theta_v)$ . We have successfully reproduced values of  $\theta_s$  for which the phenomenon of coherent scattering suppression was detected and quantified experimentally. In addition, we have examined this phenomenon over a broad range of the incident beam directions.

In terms of absolute values of the scattering angle  $\theta_s$ , there is a systematic difference between the simulated and experimentally measured data. The simulations produce the values of  $\theta_s$  that are approximately 30-35  $\mu\text{rad}$  higher. As of now, we are uncertain on the origin of this systematic discrepancy. It might be related difference in the methods of statistical analysis adopted in the current work and in Ref. [14]. We are planning to carry out a study whether this feature might originate from the algorithms implemented in MBN EXPLORER to simulate crystalline and amorphous media. However, we also believe that further experimental studies of the

phenomenon are needed.

## V. ACKNOWLEDGEMENTS

We acknowledge support by the European Commission through the N-LIGHT Project within the H2020-MSCA-RISE-2019 call (GA 872196) and the EIC Pathfinder Project TECHNO-CLS (Project No. 101046458). GRL, MMM and JRS would like to thank NA223LH-INSTEC-003 project from InSTEC-UH. We also acknowledge the Frankfurt Center for Scientific Computing (CSC) for providing computer facilities.

We are grateful to Andrea Mazzolari, Laura Bandiera and Alexey Sytov for the communications that allowed us to clarify some experimental and computational issues raised in connection with Ref. [14]

## VI. AUTHORS CONTRIBUTIONS

All the authors were involved in the preparation of the manuscript and contributed equally to this work. All the authors have read and approved the final manuscript.

### Appendix A: Basic formulae related to the Molière distribution

In what follows we outline the derivation of the 1D distribution function  $dP(\vartheta)/d\vartheta$  with respect to a planar scattering angle  $\vartheta$ , Eq. (4), starting with the Molière 2D distribution function [21] written in terms of the solid scattering angle,  $d^2P(\Omega)/d\Omega$ , where  $d\Omega = \theta d\theta d\phi$  with  $\theta \ll 1$  and  $\phi$  being the polar angles. Also presented are auxiliary formulae related to the numerical evaluation of the fitting parameter  $\theta_s$  by means of the Levenberg-Marquardt algorithm [26, 27].

When referring to the Molière distribution formalism the notations introduced in Ref. [25] are used.

Introducing planar scattering angles  $\vartheta_x = \theta \cos \phi$  and  $\vartheta_y = \theta \sin \phi$ , so that  $\theta = (\vartheta_x^2 + \vartheta_y^2)^{1/2}$  and  $d\Omega = d\vartheta_x d\vartheta_y$ , one writes the 2D distribution as follows:

$$\frac{d^2P(\vartheta_x, \vartheta_y)}{d\vartheta_x d\vartheta_y} = A \sum_{n=0}^{\infty} \left( \frac{\chi_c^2}{2\theta_s^2} \right)^n f^{(n)}(\vartheta_x, \vartheta_y). \quad (\text{A.1})$$

Here

$$\chi_c^2 \approx 4\pi N L \frac{e^4 Z(Z+1)z^2}{\varepsilon^2} \quad (\text{A.2})$$

where  $z, p, v, \varepsilon \approx pv$  are, respectively, charge of the projectile (in units of the elementary charge  $e$ ), its momentum, speed and energy calculated in the ultra-relativistic limit;  $N$  is the volume density (in  $1/\text{cm}^3$ ) of atoms in the medium,  $Z$  is their atomic number,  $L$  stands for the target's thickness. Physical meaning of  $\chi_c$  is that the total probability of a single scattering through an angle greater than  $\chi_c$  is exactly one.

The functions  $f^{(n)}(\vartheta_x, \vartheta_y)$  are given by

$$f^{(n)}(\vartheta_x, \vartheta_y) = \frac{1}{n!} \int_0^{\infty} J_0 \left( u \sqrt{\frac{\vartheta_x^2 + \vartheta_y^2}{2\theta_s^2}} \right) e^{-u^2/4} \times \left( \frac{u^2}{4} \ln \frac{u^2}{4} \right)^n u du. \quad (\text{A.3})$$

The normalization factor  $A$  can be calculated explicitly if both scattering angles  $\vartheta_{x,y}$  vary within the infinite interval  $[-\infty, +\infty]$ . The result reads  $A = 1/4\pi\theta_s^2$ .

The planar angle  $\theta_s$ , which enters Eqs. (A.1) and (A.3), is the only free parameter. It is determined by fitting the simulated or experimentally acquired data with the Molière distribution function.

To derive the 1D distribution one integrates Eq. (A.1) with respect to either variable  $\vartheta_{x,y}$  over the infinite interval. Then, using the relation (see, e.g., Eq. 6.554.3 in

Ref. [29])

$$\int_{-\infty}^{\infty} J_0 \left( a \sqrt{x^2 + b^2} \right) dx = 2 \frac{\cos(ab)}{a}, \quad (\text{A.4})$$

one writes the normalized Molière partial distribution function (PDF) with respect to a single planar angle  $\vartheta$  as follows

$$\text{PDF}(\vartheta; \theta_s) = \frac{dP(\vartheta)}{d\vartheta} = \mathcal{A} \sum_{n=0}^{\infty} \mathcal{B}^n \mathcal{C}^{(n)}(\xi) \quad (\text{A.5})$$

$$\mathcal{C}^{(n)}(\xi) = \frac{1}{n!} \int_0^{\infty} du e^{-u^2/4} \cos(u\xi) \left( \frac{u^2}{4} \ln \frac{u^2}{4} \right)^n \quad (\text{A.6})$$

where short-hand notations have been introduced:

$$\mathcal{A} = \frac{1}{\pi \sqrt{2\theta_s^2}}, \quad \mathcal{B} = \frac{\chi_c^2}{2\theta_s^2}, \quad \xi = \frac{\vartheta}{\sqrt{2\theta_s^2}}. \quad (\text{A.7})$$

Note that PDF depends parametrically on  $\theta_s$ . This dependence appears explicitly in the normalization factor  $\mathcal{A}$ , in the factors  $\mathcal{B}^n$  and in the argument  $\xi$ .

For  $n = 0$  the integral is carried out explicitly,<sup>3</sup>  $\mathcal{C}^{(0)}(\xi) = \sqrt{\pi} \exp(-\xi^2)$ . Therefore, the first term in the series (A.5) corresponds to the Gaussian distribution with variance  $\theta_s$ . Efficient numerical evaluation of the integrals  $\mathcal{C}^{(n)}$  with  $n \geq 1$  can be achieved by means of the Gauss-Laguerre quadratures (see, e.g., Ref.[27]).

Fitting the data with the distribution (A.5) implies establishing the value of the only free parameter,  $\theta_s$ , of the distribution. To determine its value one can use the Levenberg-Marquardt algorithm [26, 27]. To implement this algorithm an explicit expression for the PDF derivative with respect to  $\theta_s$  must be known. For the sake of completeness, this formula is written below:

$$\frac{d\text{PDF}}{d\theta_s} = -\frac{1}{\theta_s} \left[ \text{PDF} + \mathcal{A} \sum_{n=0}^{\infty} \mathcal{B}^n \left( 2n\mathcal{C}^{(n)} + \xi \mathcal{D}^{(n)} \right) \right] \quad (\text{A.8})$$

where

$$\mathcal{D}^{(n)} = \frac{d\mathcal{C}^{(n)}}{d\xi} = -\frac{1}{n!} \int_0^{\infty} u du e^{-u^2/4} \sin(u\xi) \left( \frac{u^2}{4} \ln \frac{u^2}{4} \right)^n \quad (\text{A.9})$$

### Appendix B: Particle Data Group

A planar rms multiple scattering angle  $\theta_0$  for an ultra-relativistic electron / positron ( $pv \approx \varepsilon$ ) moving in an amorphous medium of density  $\rho_{\text{am}}$  and thickness  $L_{\text{am}}$  can be calculated as follows (see Ref. [30], Eq. (34.16)):

$$\theta_0 = \frac{13.6 [\text{MeV}]}{\varepsilon} \sqrt{\frac{\rho_{\text{am}} L_{\text{am}}}{X_0}} \left( 1 + 0.038 \ln \frac{\rho_{\text{am}} L_{\text{am}}}{X_0} \right) \quad (\text{B.1})$$

<sup>3</sup> Explicit formula for  $\mathcal{C}^{(1)}$  is also known, see Refs. [21, 25].

Here  $X_0$  is the medium's radiation length (measured in  $\text{g}/\text{cm}^2$ ) that determines the mean distance over which a

high-energy electron loses all but  $1/e$  of its energy by bremsstrahlung, see Eq. (34.25) in [30].

- 
- [1] J. Lindhard, Influence of crystal lattice on motion of energetic charged particles. *K. Dan. Vidensk. Selsk. Mat. Fys. Medd.* **34**, 1 (1965).
- [2] J. A. Davies, J. D. McIntyre, R. L. Cushing, M. Lounsbury, The range of alkali metal ions of keV energies in aluminum. *Can. J. Chem.* **38**, 1535 (1960).
- [3] U. I. Uggerhøj, The interaction of relativistic particles with strong crystalline fields. *Rev. Mod. Phys.* **77**, 1131 (2005).
- [4] V. M. Biryukov, Yu. A. Chesnokov, V. I. Kotov, *Crystal Channeling and Its Application at High-Energy Accelerators*. Springer Science & Business Media (2013).
- [5] Andrey V. Korol, Andrey V. Solov'yov, and Walter Greiner. *Channeling and Radiation in Periodically Bent Crystals*, Second Edition. Springer Series on Atomic, Optical, and Plasma Physics **69**, Springer-Verlag, Berlin Heidelberg (2014).
- [6] A. Mazzolari, M. Romagnoni, R. Camattari, E. Bagli, L. Bandiera, G. Germogli, V. Guidi, G. Cavoto, Bent crystals for efficient beam steering of multi TeV-particle beams. Si crystal. *Eur. Phys. J. C* **78**, 720 (2018).
- [7] S. B. Dabagov and Y. P. Gladkikh, Advanced Channeling Technologies for X-ray Applications. *Rad. Phys. Chem.* **154**, 3 (2018).
- [8] W. Scandale, G. Arduini, F. Cerutti, M. Garattini, S. Giardoni, A. Masi, D. Mirarchi, S. Montesano, S. Petrucci, S. Redaelli, R. Rossi, D. Breton, L. Burmistrov, S. Dubos, J. Maalmi, A. Natchii, V. Puill, A. Stocchi, D. Sukhonos, E. Bagli, L. Bandiera, V. Guidi, A. Mazzolari, M. Romagnoni, F. Murtas, F. Addesa, G. Cavoto, F. Iacoangeli, F. Galluccio, A. G. Afonin, M. K. Bulgakov, Yu. A. Chesnokov, A. A. Durum, V. A. Maishev, Yu. E. Sandomirskiy, A. A. Yanovich, A. A. Kolomiets, A. D. Kovalenko, A. M. Taratin, G. I. Smirnov, A. S. Denisov, Yu. A. Gavrikov, Yu. M. Ivanov, L. P. Lapina, L. G. Malyarenko, V. V. Skorobogatov, G. Auzinger, T. James, G. Hall, M. Pesaesi, and M. Raymond, Comprehensive study of beam focusing by crystal devices. *Phys. Rev. Accel. Beams* **21**, 014702 (2018).
- [9] A. V. Korol and A. V. Solov'yov. *Novel Light Sources beyond Free Electron Lasers*, Springer Nature Switzerland AG (2022).
- [10] G. B. Sushko, A. V. Korol and A. V. Solov'yov, Extremely brilliant crystal-based light sources, *Europ. Phys. J. D* **76**, 166 (2022).
- [11] A. V. Korol and A. V. Solov'yov, Atomistic modeling and characterization of light sources based on small-amplitude short-period periodically bent crystals. *Nucl. Instrum. Methods B* **537**, 1 (2023).
- [12] A. I. Akhiezer and N. F. Shul'ga, Influence of multiple scattering on the radiation of relativistic particles in amorphous and crystalline media. *Sov. Phys. - Uspekhi* **30**, 197 (1987).
- [13] W. Scandale, L. S. Esposito, M. Garattini, R. Rossi, V. Zhovkovska, A. Natchii, F. Addesa, F. Iacoangeli, F. Galluccio, F. Murtas, A. G. Afonin, Yu. A. Chesnokov, A. A. Durum, V. A. Maishev, Yu. E. Sandomirskiy, A. A. Yanovich, G. I. Smirnov, Yu. A. Gavrikov, Yu. M. Ivanov, M. A. Koznov, M. V. Malkov, L. G. Malyarenko, I. G. Mamunet, J. Borg, T. James, G. Hall, and M. Pesaesi, Reduction of multiple scattering of high-energy positively charged particles during channeling in single crystals. *Eur. Phys. J. C* **79**, 99 (2019).
- [14] A. Mazzolari, A. Sytov, L. Bandiera, G. Germogli, M. Romagnoni, E. Bagli, V. Guidi, V. V. Tikhomirov, D. De Salvador, S. Carturan, C. Durigello, G. Maggioni, M. Campostrini, A. Berra, V. Mascagna, M. Prest, E. Vallazza, W. Lauth, P. Klag, and M. Tamisari, Broad angular anisotropy of multiple scattering in a Si crystal. *Eur. Phys. J. C* **80**, 63 (2020).
- [15] I. A. Solov'yov, A. V. Yakubovich, P. V. Nikolaev, I. Volkovets, and A. V. Solov'yov, MesoBioNano Explorer – A universal program for multiscale computer simulations of complex molecular structure and dynamics. *J. Comp. Phys.* **33**, 2412 (2012).
- [16] I. A. Solov'yov, A. V. Korol, and A. V. Solov'yov, *Multiscale Modeling of Complex Molecular Structure and Dynamics with MBN Explorer*. Springer International Publishing, Cham, Switzerland (2017).
- [17] G. B. Sushko, I. A. Solov'yov, and A. V. Solov'yov, Modeling MesoBioNano systems with MBN Studio made easy. *J. Mol. Graph. Model.* **88**, 247 (2019).
- [18] MBN Explorer and MBN Studio Software at <http://mbnresearch.com>
- [19] Andrei V. Korol, Gennady B. Sushko, and Andrey V. Solov'yov, All-atom relativistic molecular dynamics simulations of channeling and radiation processes in oriented crystals. *Europ. Phys. J. D* **75**, 107 (2021).
- [20] G. B. Sushko, V. G. Bezchastnov, I. A. Solov'yov, A. V. Korol, W. Greiner, and A. V. Solov'yov, Simulation of ultra-relativistic electrons and positrons channeling in crystals with MBN Explorer. *J. Comp. Phys.* **252**, 404 (2013).
- [21] G. Molière, Theorie der Streuung schneller geladener Teilchen I: Einzelstreuung am abgeschirmten Coulombfeld. *Z. f. Naturforsch* **A2**, 133 (1947).
- [22] L. Fernandes Pacios, Analytical Density-Dependent Representation of Hartree-Fock Atomic Potentials. *J. Comp. Chem.* **14**, 410 (1993).
- [23] P. A. Doyle and P. S. Turner, Relativistic Hartree-Fock X-ray and Electron Scattering Factors. *Acta Cryst. A* **24**, 390 (1968).
- [24] G. V. Dedkov, Interatomic potentials of interactions in radiation physics *Sov. Phys. - Uspekhi* **38**, 877 (1995).
- [25] H. A. Bethe, Molière's Theory of Multiple Scattering. *Phys. Rev.* **89**, 1256 (1953).
- [26] D. W. Marquardt, An Algorithm for Least-Squares Estimation of Nonlinear Parameters. *J. Soc. Ind. Appl. Math.* **11**, 431 (1963).
- [27] W. H. Press, B. P. Flannery, S. A. Teukolsky and W. T. Vetterling, *Numerical Recipes. The Art of Scientific Computing*, University Press, Cambridge (1988).
- [28] Sytov, A. and Tikhomirov, V. CRYSTAL simulation code and modeling of coherent effects in a bent crystal at the



- LHC. *Nucl. Instrum. Methods B* **355**, 383 (2015). (2022).
- [29] I. S. Gradshtein, I. M. Ryzhik. *Table of Integrals, Series, and Products* Elsevier Academic Press (2014).
- [30] R. L. Workman *et al.* [Particle Data Group], Review of Particle Physics. *Progr. Theor. Exp. Phys* **2022**, 083C01